



JST12C-1000

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4.5	kV
--	----------	-----	----

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_H	$I_T=500mA$		MAX.	35	mA

dV/dt $V_D=670V$ Gate Open $T_j=125$

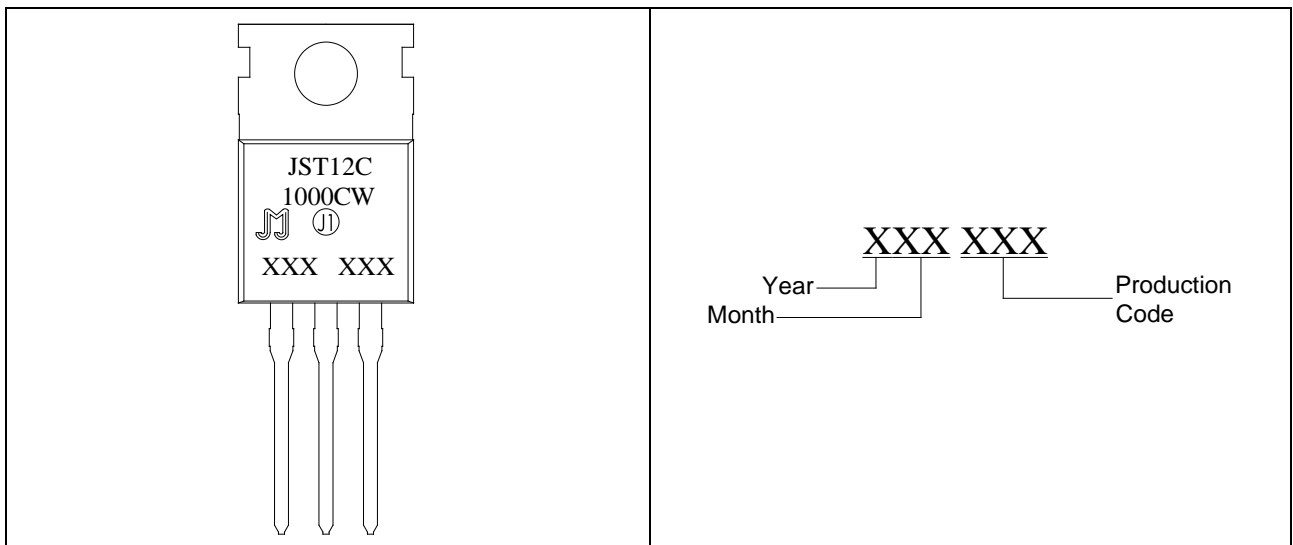
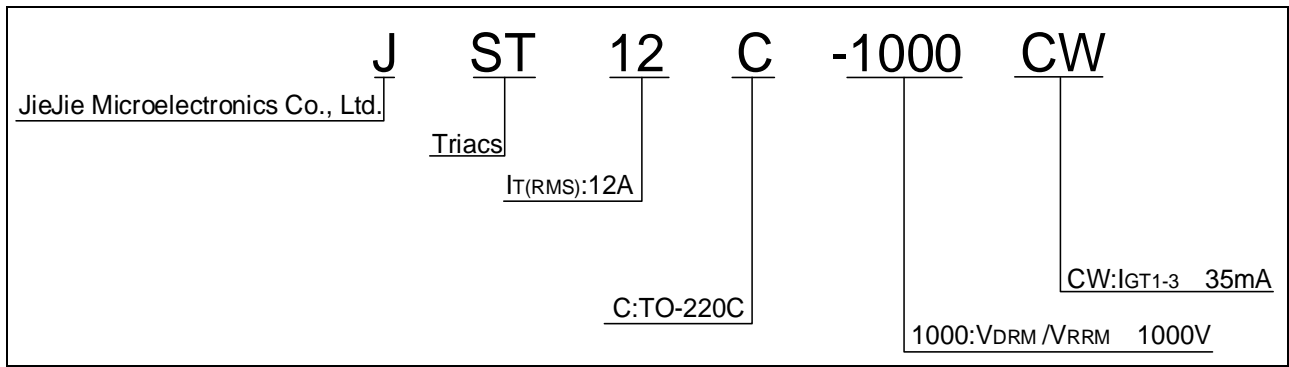


FIG.1 Maximum power dissipation versus RMS on-state current

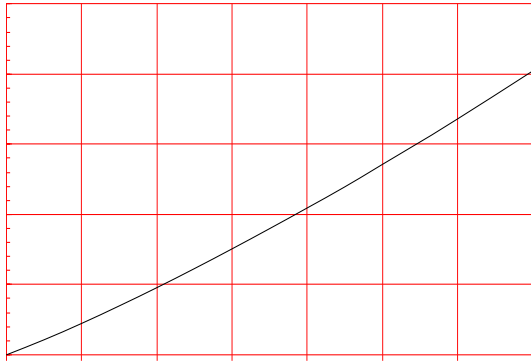


FIG.2: RMS on-state current versus case temperature

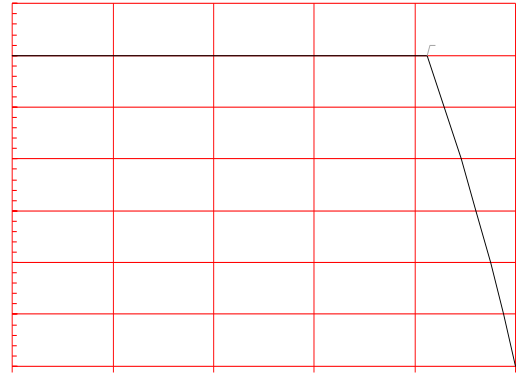
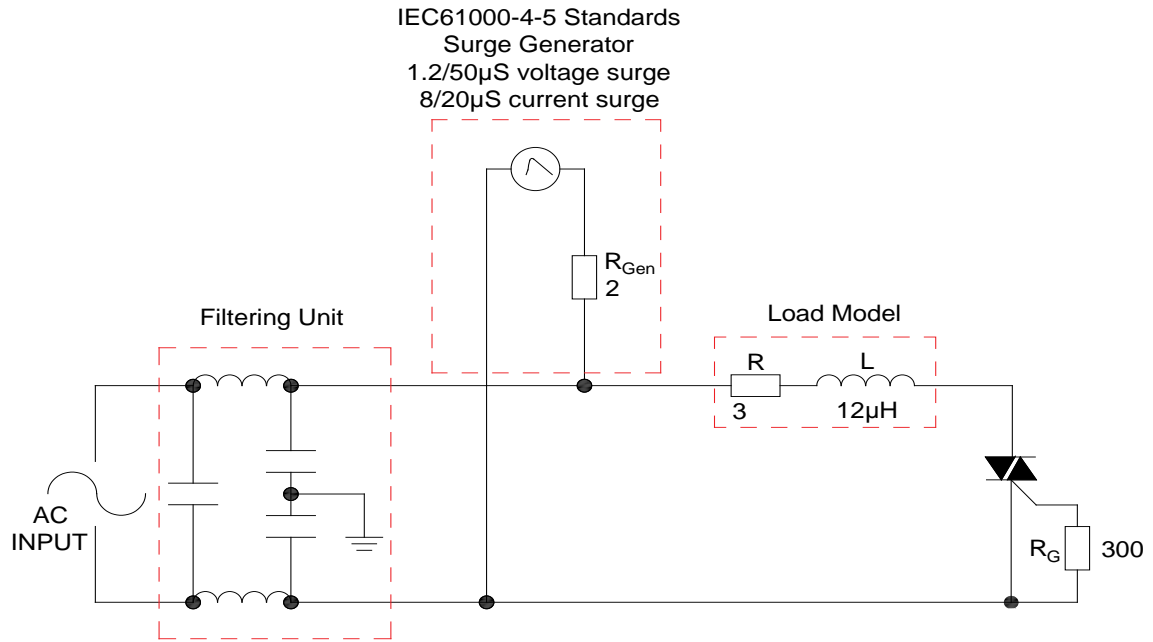


FIG.3: Surge peak on-state current versus number of cycles

FIG.4: On-state characteristics

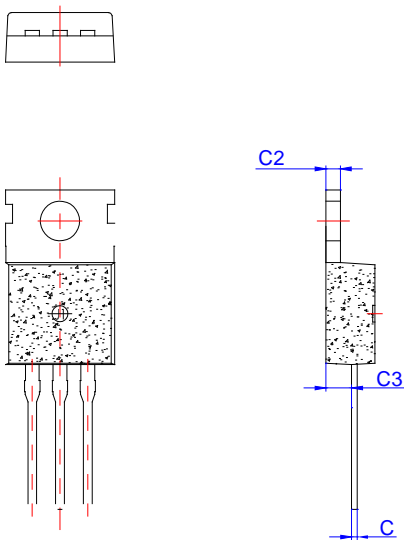
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST12C-1000CW	1000	35	TO-220C	50	Tube


Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.